



DMTH6016LPD

60V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	$19mΩ @ V_{GS} = 10V$	33.2A
	$28m\Omega$ @ VGS = 4.5V	28A

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production –
 Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Data Sheet (DMTH6016LPDQ)

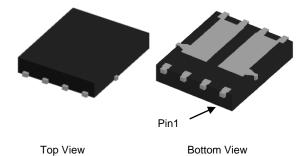
Description and Applications

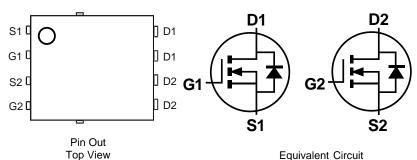
This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$, yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Engine Management Systems
- Body Control Electronics
- DCDC Converters

Mechanical Data

- Case: PowerDI[®]5060-8 (Type C)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)





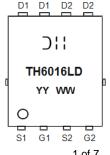
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH6016LPD-13	PowerDI5060-8 (Type C)	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



⊃¦¦ = Manufacturer's Marking TH6016LD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 18 = 2018) WW = Week (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 6)	$T_C = +25$ °C $T_C = +100$ °C	I _D	33.2 23.7	А
Continuous Drain Current (Note 5) $T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$		I _D	9.2 6.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	50	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	31	Α	
Avalanche Current, L = 0.1mH	I _{AS}	15.3	Α	
Avalanche Energy, L = 0.1mH	E _{AS}	11.7	mJ	

Thermal Characteristics

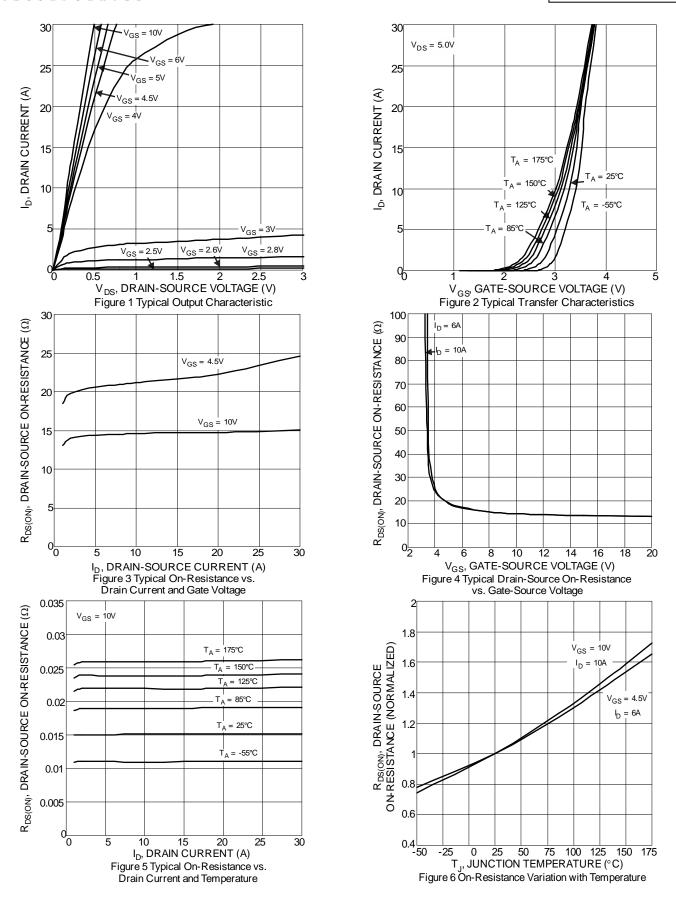
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	58	°C/W
Total Power Dissipation (Note 6)	P_D	37.5	W
Thermal Resistance, Junction to Case (Note 6)	R _{eJC}	4	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)				•	•	•	
Gate Threshold Voltage	$V_{GS(TH)}$	1	_	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		_	14.5	19	0	V _{GS} = 10V, I _D = 10A	
Static Drain-Source On-Resistance	R _{DS(ON)}		20.9	28	mΩ	$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V_{SD}	-	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	864	_	pF		
Output Capacitance	Coss	_	282	_	pF	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	27	_	pF	T = TIMHZ	
Gate Resistance	Rg	_	1.3	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	8.4	_	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	_	17	_	nC	nC	
Gate-Source Charge	Q_{gs}	_	3.1	_	nC	$V_{DS} = 30V, I_{D} = 10A$	
Gate-Drain Charge	Q _{gd}	_	4.3	_	nC	1	
Turn-On Delay Time	t _{D(ON)}	_	3.4	_	ns		
Turn-On Rise Time	t _R		5.2	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 10A, R_{g} = 6\Omega$	
Turn-Off Delay Time	t _{D(OFF)}		13	_	ns		
Turn-Off Fall Time	t _F		7	_	ns		
Body Diode Reverse Recovery Time	t _{RR}		22	_	ns	1 404 3744 40047	
Body Diode Reverse Recovery Charge	Q_{RR}	_	11	_	nC	$I_F = 10A$, di/dt = 100A/ μ s	

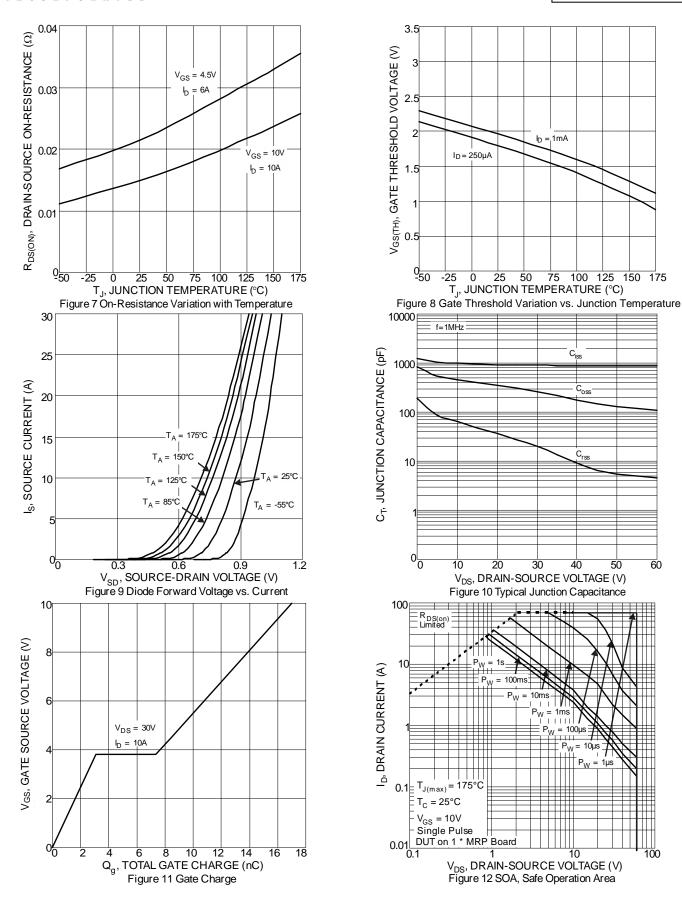
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:



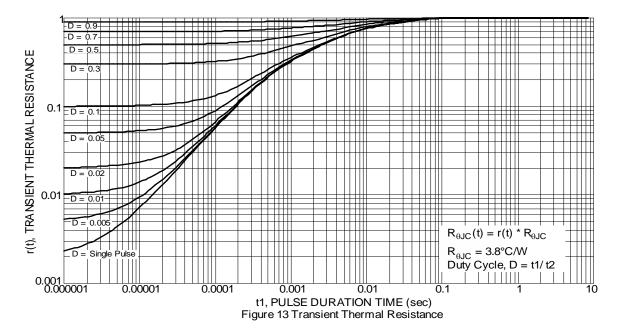










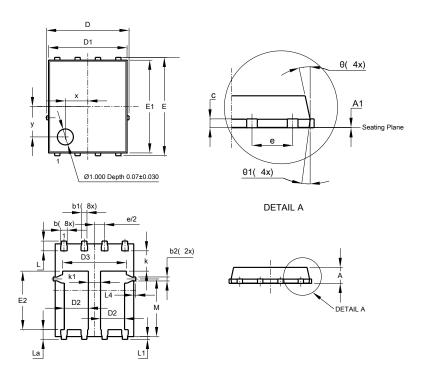




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type C)

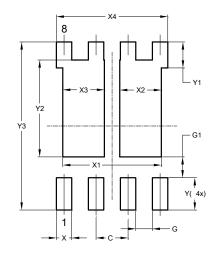


PowerDI5060-8 (Type C)					
Dim	Min Max Ty				
Α	0.90	1.10	1.00		
A1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	ţ	5.15 BSC	;		
D1	4.85	4.95	4.90		
D2	1.40	1.60	1.50		
D3	-	-	3.98		
Е	6.15 BSC				
E1	5.75	5.85	5.80		
E2	3.56	3.76	3.66		
е	1.27BSC				
k	-	-	1.27		
k1	0.56	-	-		
L	0.51	0.71	0.61		
La	0.51	0.71	0.61		
L1	0.05	0.20	0.175		
L4	-	-	0.125		
M	3.50	3.71	3.605		
Х	-	-	1.400		
у	-	-	1.900		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type C)



Dimensions	Value			
פווטופווסוטווט	(in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	3.910			
X2	1.650			
Х3	1.650			
X4	4.420			
Υ	1.270			
Y1	1.020			
Y2	3.810			
Y3	6.610			



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